

DIT 3 1 2003 A

ABSTRACT OF THE DISCLOSURE

Disclosed are methods of processing a semiconductor structure, involving the steps of depositing a light-degradable surface coupling agent on a semiconductor substrate; depositing a resist over the light-degradable surface coupling agent; irradiating portions of the resist, wherein the light-degradable surface coupling agent under the irradiated portions of the resist at least partially decomposes; and developing the resist.

ARCEINED ARCHIVED

REPLACEMENT SHEET